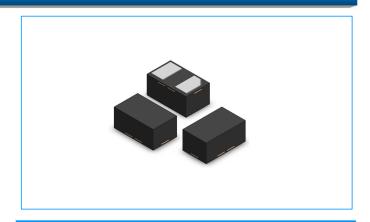


### ESD3.3V88D-LCDN

### **Description**

The ESD3.3V88D-LCDN is low capacitance TVS arrays designed to protect high speed data interfaces. This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from over-voltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients)

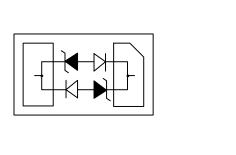


#### **Feature**

- ♦ 225 Watts Peak Pulse Power per Line (tp=8/20µs)
- ◆ Protects One Bidirectional I/O Line
- Low clamping voltage
- Working voltages : 3.3V
- ◆ IEC61000-4-4 (EFT) 40A (5/50ηs)
- ◆ IEC61000-4-5 (LIGHTING) 16A (8/20µs)
- ◆ IEC61000-4-2(ESD):±30kV (air discharge)

±30kV (contact discharge)

## **Functional Diagram**



### **Applications**

- ♦ 10/1000 Gigabit interface
- Cell Phone Handsets and Accessories
- ◆ Microprocessor based equipment
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Peripherals
- Pagers

### **Mechanical Data**

- ◆ SOD-882/DFN1006 (1.0x0.6x0.5mm) Package
- Molding Compound Flammability Rating: UL 94V-O
- ◆ Weight 0.5 Milligrams (Approximate)
- ◆ Lead Finish : Lead Free

#### **Mechanical Characteristics**

Symbol	Parameter	Value	Units
P <sub>PP</sub>	Peak Pulse Power (tp=8/20µs waveform)	225	Watts
T∟	Lead Soldering Temperature	260 (10 sec.)	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to +150	°C
TJ	Operating Junction Temperature Range	-40 to +125	°C



## ESD3.3V88D-LCDN

### Electrical Characteristics (@ 25℃ Unless Otherwise Specified )

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Reverse Working Voltage	V <sub>RWM</sub>				3.3	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> =1mA;	3.5	-		V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =3.3V, T=25°C;	1		0.1	μΑ
Positive Clamping	V <sub>C</sub>	I <sub>PP</sub> =1Α, T <sub>P</sub> =8/20μs;			5.0	V
Voltage	VC	I <sub>PP</sub> =15A,T <sub>P</sub> =8/20μs;		12	15	V
Junction capacitance	CJ	V <sub>R</sub> = 0V, f = 1MHz;		15		pF

### **Characteristic Curves**

Fig1. 8 x 20µs Pulse Waveform

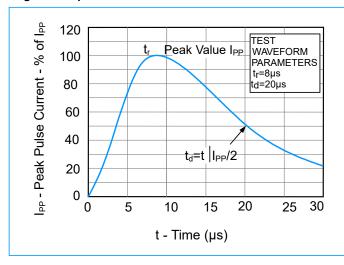


Fig2. Power Derating Curve

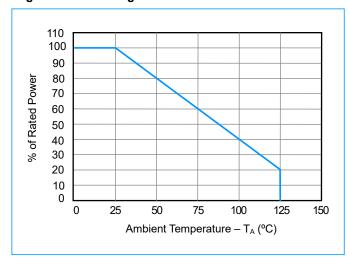


Fig3. ESD Pulse Waveform (according to IEC 61000-4-2)

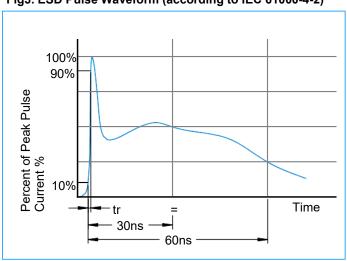
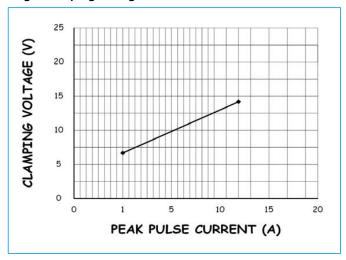


Fig4.Clamping Voltage vs. Peak Pulse Current



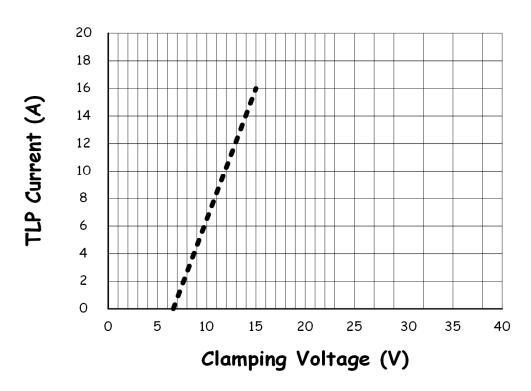


### ESD3.3V88D-LCDN

### **Transmission Line Pulse (TLP)**

Transmission Line Pulse (TLP) is a measurement technique used in the Electrostatic Discharge (ESD) arena to characterize performance attributes of devices under ESD stresses. TLP is able to obtain current versus voltage (I–V) curves in which each data point is obtained with a 100ns long pulse, with currents up to 40 A. TLP was first used in the ESD field to study human body model (HBM) in integrated circuits, but it is an equally valid tool in the field of system level ESD. The applicability of TLP to system level ESD is illustrated in Figure 1, which compares an 8KV IEC 61000–4–2 current waveform with TLP current pulses of 8 and 16 A. The current levels and time duration for the pulses are similar and the initial rise time for the TLP pulse is comparable to the rise time of the IEC 61000–4–2's initial current spike. This application note will give a basic introduction to TLP measurements and explain the data sheet parameters extracted from TLP for SDI Technology's protection products.

# TLP Characteristic

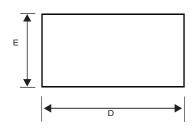


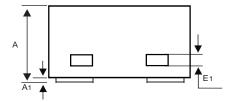


# ESD3.3V88D-LCDN

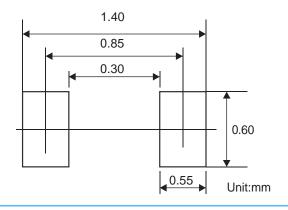
# SOD-882/DFN1006 Package Outline & Dimensions

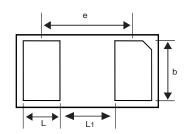
### SOD-882/DFN1006





# **Suggested PAD Layout**





Symbol	Millimeters			
Symbol	Min	Nom	Max	
Α	0.450	0.500	0.550	
A1	0	0.020	0.050	
E1	0.013	0.063	0.113	
D	0.900	1.000	1.100	
E	0.500	0.600	0.700	
е	0.65BSC			
L	0.150	0.250	0.350	
b	0.400	0.500	0.600	
L1	0.300	0.400	0.500	

### **Ordering Information**

Device	Marking	Package	Quantity	Reel Size
ESD3.3V88D-LCDN	ES	SOD-882/DFN1006	10,000pcs/Reel	7 inch